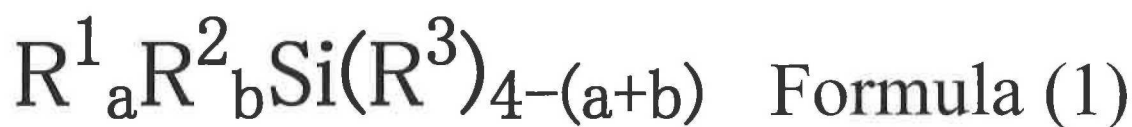


ABSTRACT

SILICON-CONTAINING RESIST UNDERLAYER FILM-FORMING COMPOSITION
HAVING ORGANIC GROUP HAVING ALIPHATIC POLYCYCLIC STRUCTURE

There are provided a resist underlayer film and a composition for forming the
5 same able to form an excellent resist pattern when an upperlayer resist is exposed and
then developed by an alkaline developer or an organic solvent.

A resist underlayer film-forming composition for lithography having an aliphatic
polycyclic structure comprising, as a silane, a hydrolyzable silane, a hydrolysis product
thereof, a hydrolysis-condensation product thereof, or a combination thereof, in which the
10 aliphatic polycyclic structure is a structure which a hydrolyzable silane of Formula (1):



(where R^1 is an organic group having an aliphatic polycyclic structure and bonded to a Si
atom through a Si-C bond; R^3 is an ethoxy group; a is an integer of 1; b is an integer of 0
15 to 2; and $a + b$ is an integer of 1 to 3) has, or a structure included in a compound added as
an aliphatic polycyclic compound, an aliphatic polycyclic dicarboxylic acid, or an
aliphatic polycyclic dicarboxylic acid anhydride, each optionally having a double bond, a
hydroxy group, or an epoxy group.